MUR2080CT MURF2080CT MUR2080D1 MUR2080M1

POLYIMIDE PASSIVATED SUPER F AST RECTIFIER

Reverse Voltage - 800 Volts

Forward Current - 20.0Amperes

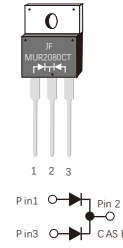
SEMICONDUCTOR

FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V -0
- Fast switching for high efficiency
- Low forward voltage drop
- Single rectifier construction
- High surge capability
- For use in low voltage ,high frequency inverters, free wheeling ,and polarity protection applications
- High temperature soldering guaranteed:260°C/10 seconds, 0.25"(6.35mm)from case
- Component in accordance to RoHS 2015/863/EU

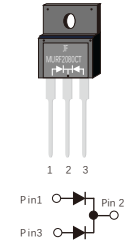
TO-220AB

MUR2080CT



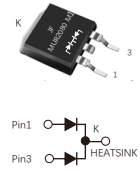
ITO-220AB

MURF2080CT



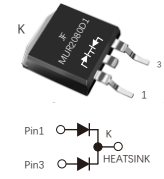
TO-252

MUR2080M1



TO-263

MUR2080D1



MECHANICAL D ATA

- Case: JEDEC TO-220AB、ITO-220AB、TO-263、TO-252 molded plastic body
- Terminals: Lead solderable per MIL-STD-750,method 2026
- Polarity: As marked
- Mounting Position: Any

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Ratings at 25 ℃ ambient temperature unless otherwise specified ,Single phase ,half wave ,resistive or inductive load. For capacitive load,derate by 20%.)

Parameters		Symbols	Value				Units
Maximum repetitive peak reverse voltage		V_{RRM}	800				Volts
Maximum RMS voltage		V_{RMS}	560				Volts
Maximum DC blocking voltage		V_{DC}	800				Volts
Maximum average forward rectified current(see Fig.1)	Per leg	$I_{(AV)}$	10				Amps
	Total device		20				
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)		I_{FSM}	150				Amps
Forward voltage (Note 1)	I_F=3A	V_F	TYP.	1.7	MAX.	/	Volts
	I_F=5A		TYP.	1.9	MAX.	/	
	I_F=10A		TYP.	2.1	MAX.	2.5	
Reverse current at rated DC blocking voltage(Note 1)	T_A=25°C	I_R	TYP.	1	MAX.	5	μA
	T_A=125 °C		TYP.	10	MAX.	50	
Maximum Reverse Recovery Time (Note 2)		Trr	35				ns
Typical thermal resistance		$R_{\theta JC}$	TO-220AB、TO-263、TO-252		2.5		°C/W
			ITO-220AB		4.5		
Operating junction temperature range		T_J	-55 to+150				°C
Storage temperature range		T_{STG}	-55 to+150				°C

Notes: 1. Pulse test: 300 μs pulse width,1% duty cycle

2. Reverse recovery test conditions I_F=0.5A,I_R=1.0A, Irr=0.25A

FIG.1-FORWARD CURRENT DERATING CURVE

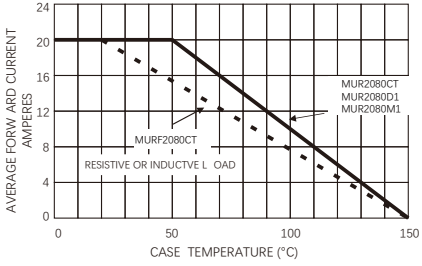


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

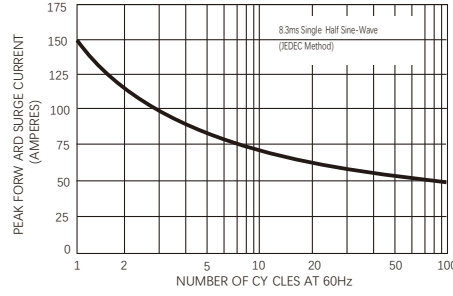


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

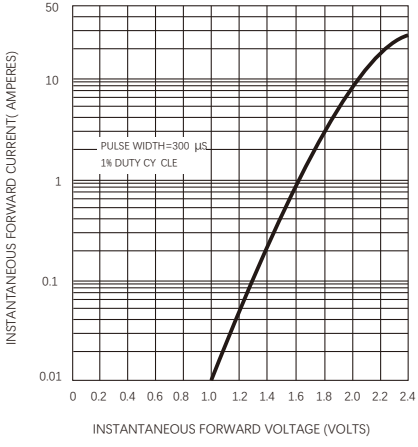
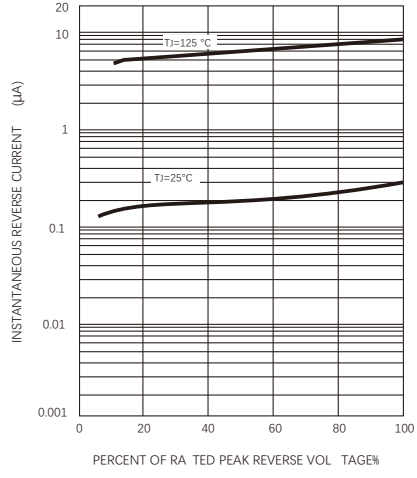


FIG.4-TYPICAL REVERSE CHARACTERISTICS

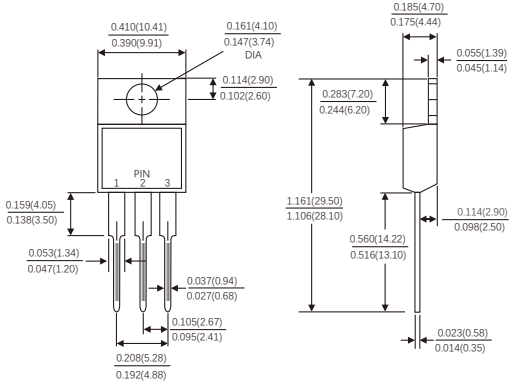


SEMICONDUCTOR

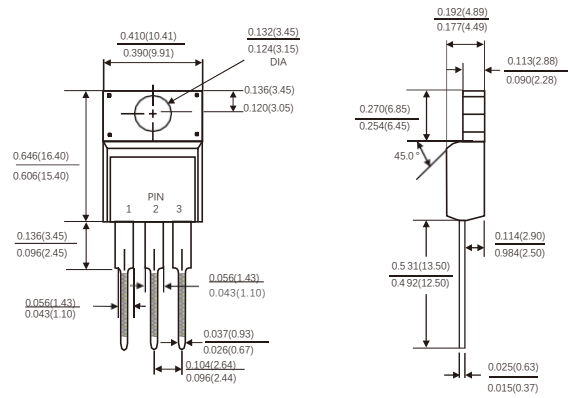
PACKAGE OUTLINE DIMENSIONS

Dimensions in inches and (millimeters)

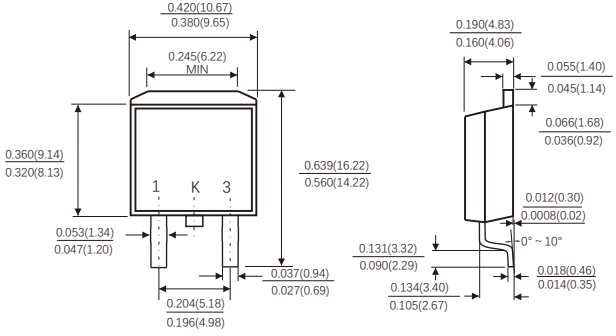
TO-220AB



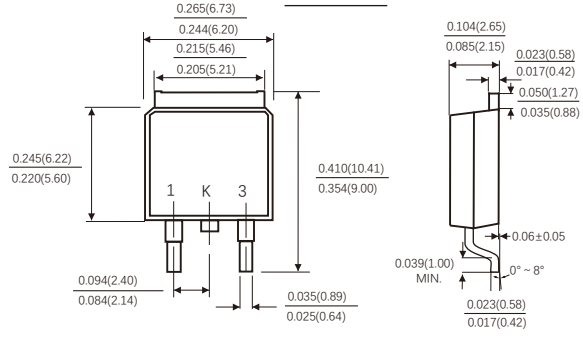
ITO-220AB



TO-263

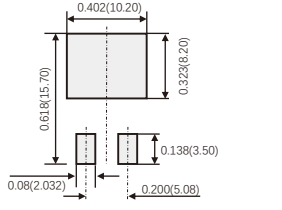


TO-252



Suggested Pad Layout

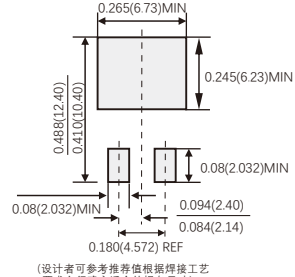
(TO-263)



(设计者可参考推荐值根据焊接工艺
要求自行确定适合的焊盘尺寸)
(Designers can refer to the recommended
values according to the manufacturing process
requirements to determine the appropriate pad size)

Suggested Pad Layout

(TO-252)



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